TENTATIVE

TOSHIBA Photocoupler GaAlAs Ired + Photo-IC

TLP114A(IGM)

Transistor Invertor
Inverter For Air Conditioner
Line Receiver
Ipm Interfaces

The TOSHIBA mini flat coupler TLP114A is a small outline coupler, suitable for surface mount assembly.

TLP114A consists of a high output power GaAlAs light emitting diode, optically coupled to a high speed detector of one chip photo diode–transistor.

TLP114A(IGM) has no internal base connection, and a faraday shield integrated on the photodetector chip provides an effective common mode noise transient immunity.

TLP114A(IGM) guarantees minimum and maximum of propagation delay time, switching time dispersion, and high common mode transient immunity. There for TLP114A(IGM) is suitable for isolation interface between IPM(intelligent power module) and control IC circuits in motor control application.

- Isolation voltage: 3750V_{rms}(min.)
- Common mode transient immunity

 $\begin{array}{l} :\pm 10 kV/\mu s(min.) \\ @V_{\mbox{CM}} = 1500V \end{array}$

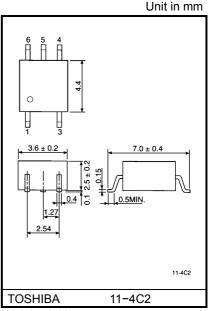
• Switching time: t_{pHL} , t_{pLH} =0.1 $\mu s(min.)$ =0.8 $\mu s(max.)$

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@I_F=10mA, V_{CC}=15V,

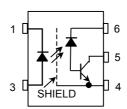
R_L=20kΩ, Ta=25°C

- Switching time dispersion: 0.7μs(max.) (|t_{pLH}-t_{pHL}|)
- TTL compatible
- UL recognized: UL1577, file no.E67349



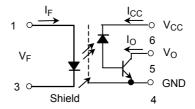
Weight: 0.09g

Pin Configuration(top view)



- 1 : Anode
- 3 : Cathode
- 4 : Emitter (GND)
- 5 : Collector (Output)
- 6 : V_{CC}

Schematic



Maximum Ratings(Ta = 25°C)

	Characteristic	Symbol	Rating	Unit	
Forward current		(Note 1)	lF	20	mA
Ω	Pulse forward current	(Note 2)	I _{FP}	40	mA
LED	Peak transient forward current	(Note 3)	I _{FPT}	1	Α
Reverse voltage			V _R	5	V
	Output current		ΙO	8	mA
'n	Peak output current		I _{OP}	16	mA
Detector	Output voltage		Vo	-0.5~20	V
ă	Supply voltage		V _{CC}	-0.5~30	V
	Output power dissipation	(Note 4)	PO	100	mW
Оре	Operating temperature range		T _{opr}	-55~100	°C
Stor	Storage temperature range			-55~125	°C
Lea	Lead soldering temperature(10s)			260	°C
Isola	Isolation voltage(AC, 1min., R.H.≤60%, Ta=25°C) (Note 5)			3750	Vrms

(Note 1): Derate 0.36mA above 70°C.

(Note 2): 50% duty cycle, 1ms pulse width.

Derate 0.72mA / °C above 70°C.

(Note 3): Pulse width PW $\leq 1\mu s$, 300pps.

(Note 4): Derate 1.8mW / °C above 70°C.

(Note 5): Device considerd a two terminal device: pins1, 3 shorted together and pins4, 5, 6 shorted together.

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Electrical Characteristics(Ta = 25°C)

Characteristic		Symbol	Test Condition	Min.	Тур.	Max.	Unit
TED	Forward voltage	V _F	I _F =16mA	1.22	1.42	1.72	V
	Forward voltage temperature coefficient	ΔV _F / ΔTa	I _F =16mA		-2	_	mV / °C
	Reverse current	I _R	V _R =3V	_	_	10	μΑ
	Capacitance between terminal	СТ	V _F =0, f=1MHz	_	30	-	pF
Detector	High level output current	I _{OH(1)}	I _F =0mA, V _{CC} =V _O =5.5V	-	3	500	nA
		I _{OH(2)}	I _F =0mA, V _{CC} =30V V _O =20V	_	_	5	μΑ
		ІОН	I _F =0mA, V _{CC} =30V V _O =20V, Ta=70°C	ı	_	50	μΑ
	High level supply current	Іссн	I _F =0mA, V _{CC} =30V	_	0.01	1	μА
	Supply voltage	V _{CC}	I _{CC} =0.01mA	30	_	_	V
	Output voltage	V _O	I _O =0.5mA	20	_	_	V

Coupled Electrical Characteristics(Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Current transfer ratio	l lo/le	I _F =10mA, V _{CC} =4.5V V _O =0.4V	25	35	75	. %
		I _F =16mA, V _{CC} =4.5V V _O =0.4V, Ta=-25~100°C	15	_	_	
Low level output voltage	V _{OL}	I _F =10mA, V _{CC} =4.5V I _O =2.4mA	ı	ı	0.4	V

Isolation Characteristics(Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	Cs	V=0, f=1MHz (Note 5)	_	8.0	_	pF
Isolation resistance	R _S	R.H.≤60%, V _S =500V (Note 5)	5×10 ¹⁰	10 ¹⁴		Ω
	BVS	AC, 1 minute	3750	_	_	Vrms
Isolation voltage		AC, 1 second, in oil	_	10000	_	VIIIIS
		DC, 1 minute, in oil	_	10000	_	Vdc

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Switching Characteristics(Ta = 25°C, V_{CC} = 15V)

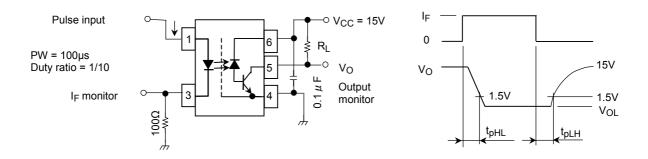
Characteristic		Symbol	Test Cir– Cuit	Test Condition	Min.	Тур.	Max.	Unit
Propagation delay time		t _{pHL}	-	I_F =0 \rightarrow 10mA, R _L =20kΩ	0.1	0.45	0.8	μs
(H→ L) Propagation delay time	H→ L)	t _{pLH}		I_F =0→ 10mA, R_L =20kΩ Ta =0~85°C	0.1	0.45	0.9	
(L→ H)				I_F =0 \rightarrow 10mA, R_L =20k Ω Ta= -25 ~100°C	0.1	0.45	1.0	
				I_F =10 \rightarrow 0mA, R_L =20kΩ	_	0.15	0.7	μѕ
Switching time dispersion between on		t _{pLH} =t _{pHL}		I_F =10 \rightarrow 0mA, R_L =20k Ω Ta=0~85°C	_	0.25	0.8	
and off				I_F =10 \rightarrow 0mA, R_L =20k Ω Ta= -25 ~100°C	_	0.25	0.9	
Common mode transient immunity at logic high output	(Note 6)	CM _H	2	I_F =0mA V_{CM} =1500 V_{p-p} R_L =20k Ω	10000	15000	_	V / µs
Common mode transient immunity at logic low output	(Note 6)	CML	2	I_F =10mA V_{CM} =1500 V_{p-p} R_L =20k Ω	-10000	-15000	_	V / µs

(Note 6): CM_L is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic low state (V_O<1V).

CM_H is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic high state (V_O<4V).

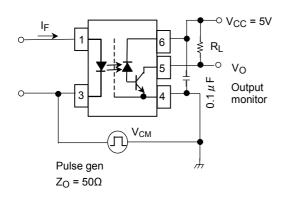
(Note 7): Maximum electrostatic discharge voltage for any pins: 100V (C=200pF, R=0).

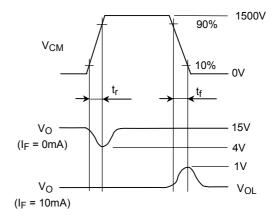
Test Circuit 1: Switching Time Test Circuit



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Test Circuit 2: Common Mode Noise Immunity Test Circuit





$$\text{CM}_{H} = \frac{1200(V)}{t_{f}(\mu s)}, \text{CM}_{L} = \frac{1200(V)}{t_{f}(\mu s)}$$

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